

Amendments to the Claims

1. (Original) A sputtering component comprising a sputtering surface, at least 99 atomic% of the sputtering surface consisting of a single phase corresponding to a solid solution of two or more elements in elemental form; each of the two or more elements being selected from groups 1, 5, 6, 8, 9 and 10 of the periodic table.

2. (Original) The sputtering component of claim 1 wherein at least 99.9 atomic% of the sputtering surface consists of the single phase.

3. (Original) The sputtering component of claim 1 wherein an entirety of the sputtering surface consists of the single phase.

4. (Original) The sputtering component of claim 1 as a physical vapor deposition target.

5. (Original) The physical vapor deposition target of claim 4 having a total volume, and wherein at least 99 atomic% of the total volume consists of the single phase.

6. (Original) The physical vapor deposition target of claim 5 wherein at least 99.9 atomic% of the total volume consists of the single phase.

7. (Original) The physical vapor deposition target of claim 5 wherein an entirety of the total volume consists of the single phase.

8. (Original) A thin film sputter-deposited from the sputtering component of claim 1.

9. (Original) The sputtering component of claim 1 wherein the two or more elements include at least two elements selected from group 1 of the periodic table.
10. (Original) The sputtering component of claim 1 wherein the two or more elements are selected only from group 1 of the periodic table.
11. (Original) A thin film sputter-deposited from the sputtering component of claim 10.
12. (Original) The sputtering component of claim 10 wherein the two or more elements consist of Cs and Rb.
13. (Original) The sputtering component of claim 1 wherein the two or more elements include at least two elements selected from group 5 of the periodic table.
14. (Original) The sputtering component of claim 1 wherein the two or more elements are selected only from group 5 of the periodic table.
15. (Original) A thin film sputter-deposited from the sputtering component of claim 14.
16. (Original) The sputtering component of claim 14 wherein each of the two or more elements are selected from the group consisting of Ta, Nb, and V.
17. (Original) The sputtering component of claim 1 wherein the two or more elements include at least two elements selected from group 6 of the periodic table.

18. (Original) The sputtering component of claim 1 wherein the two or more elements are selected only from group 6 of the periodic table.

19. (Original) A thin film sputter-deposited from the sputtering component of claim 18.

20. (Original) The sputtering component of claim 1 wherein the two or more elements include at least two elements selected from groups 8, 9 and 10 of the periodic table.

21. (Original) The sputtering component of claim 1 wherein the two or more elements are selected only from groups 8, 9 and 10 of the periodic table.

22. (Original) A thin film sputter-deposited from the sputtering component of claim 21.

23. (Original) The sputtering component of claim 21 wherein the solution is a binary combination selected from the group consisting of Fe/Os, Fe/Ru, Co/Ir, Co/Rh, Ir/Rh, Ni/Pd, Ni/Pt, Co/Ni and Pd/Pt.

24. (Original) The sputtering component of claim 1 wherein the solution is Ta/Mo.

25. (Original) The sputtering component of claim 1 wherein the solution is Ta/W.

26. (Original) The sputtering component of claim 1 wherein the solution is Cr/Fe.

27. (Original) A sputtering component comprising a single phase solid solution comprising elemental Cu and elemental Ni.

Claims 28-41 (Cancelled)